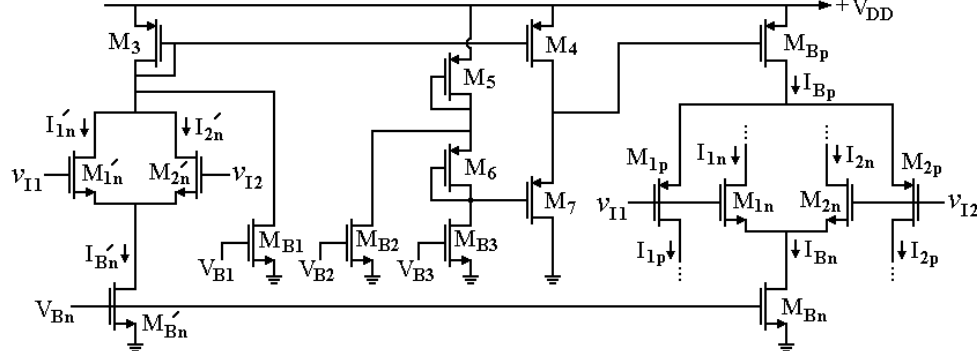


The second circuit using the same method has a different topology but makes use of a similar approach (A loop along  $V_{GS}$  voltages).



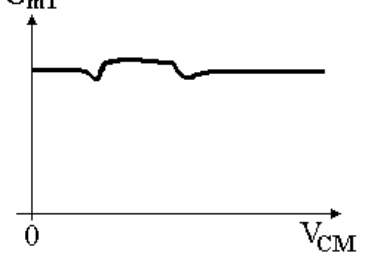
$M_{Bn}$  supplies an exact copy of  $I_{Bn}$  to  $M_3$ , in addition to  $I_{B1}$ . Thus,  $|I_7| = |I_4| = |I_3| = I_{Bn} + I_{B1}$ . Also,  $|I_5| = I_{B2} + I_{B3}$  and  $|I_6| = I_{B3}$  can be observed. It is obvious that,  $|V_{GSBp}| + |V_{GS7}| = |V_{GS5}| + |V_{GS6}|$ . Then, if all these four transistors are matched, we obtain

$$\sqrt{I_{Bp}} + \sqrt{(I_{Bn} + I_{B1})} = \sqrt{(I_{B2} + I_{B3})} + \sqrt{I_{B3}}$$

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Then, choosing  $I_{B1} \ll I_{Bn}$  will be enough for  $G_{mT}$  achieving  $\sqrt{I_{Bp}} + \sqrt{I_{Bn}} = \text{constant}$ .

Compared to the first circuit, this circuit seems to be achieving a less  $G_{mT}$  error along the CM input range; probably because a loop along  $V_{GS}$  voltages of pMOS transistors (free of body effect) are utilized. The relative  $G_{mT}$  error can be kept less than 10%.



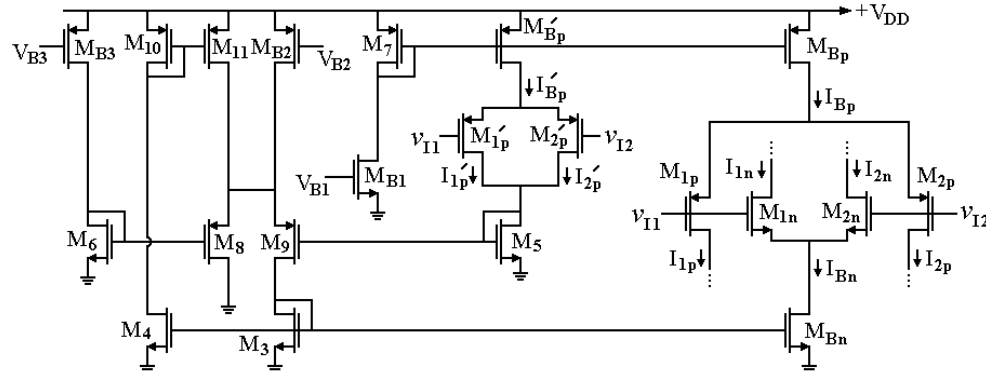
**A note by A.Z.:** Actually, using only  $I_{B3}$  would be sufficient;  $I_{B1}$  and  $I_{B2}$  seem useless. In this case, mathematically,  $\sqrt{I_{Bp}} + \sqrt{I_{Bn}} = \text{constant}$  is achieved more accurately ( $\sqrt{I_{Bp}} + \sqrt{I_{Bn}} = 2\sqrt{I_{B3}}$ ).

However,  $I_{B1}$  and  $I_{B2}$  are probably used for **trimming** purposes. *i.e.* to compensate for the errors caused by the deviation from square law, body effect,  $\beta_n$  vs.  $\beta_p$  inequalities, etc.

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**Try to keep  $\sqrt{(\beta_n I_{Bn})} + \sqrt{(\beta_p I_{Bp})}$  fixed ( $\beta_n = \beta_p$  not required) :**

As an example, the constant- $g_m$  rail-to-rail input stage below will be explained.



The auxiliary differential pair  $M_{1p}$ - $M_{2p}$  receives a copy of  $I_{Bp}$  and this current is conveyed to  $M_5$ . Then, after some processing, a proper  $I_{Bn}$  is obtained to achieve a **constant**  $\sqrt{(\beta_n I_{Bn})} + \sqrt{(\beta_p I_{Bp})}$ .

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Notice that,  $V_{GS5} + |V_{GS9}| = V_{GS6} + |V_{GS8}|$ . We can rewrite this as,

$$\sqrt{(2I_5/\beta_5) + V_{TH5}} + \sqrt{(2|I_9|/\beta_9) + |V_{TH9}|} = \sqrt{(2I_6/\beta_6) + V_{TH6}} + \sqrt{(2|I_8|/\beta_8) + |V_{TH8}|}$$

- Since  $V_{SB5}$  and  $V_{SB6}$  are zero,  $V_{TH5}$  and  $V_{TH6}$  are not affected by body effect; thus they are equal (equal to  $V_{TH0}$ ).
- Also, since sources of  $M_8$  and  $M_9$  are tied to the same node,  $V_{SB8}$  and  $V_{SB9}$  are equal (*i.e.*,  $V_{TH8}$  and  $V_{TH9}$  are modified equally by body effect). So, - *although it is possible* - there is no requirement for separate wells to obtain  $V_{TH8} = V_{TH9}$  equality.

As a result of  $V_{TH}$  equalities we obtain

$$\sqrt{(2I_5/\beta_5)} + \sqrt{(2|I_9|/\beta_9)} = \sqrt{(2I_6/\beta_6)} + \sqrt{(2|I_8|/\beta_8)}$$

Note also that,  $I_5 = I_{Bp}$ ,  $I_6 = I_{B3}$ ,  $|I_9| = I_{Bn}$  and  $|I_8| = I_{Bn} + I_{B2} - |I_9| = I_{B2}$ . So,

$$\sqrt{(2I_{Bp}/\beta_5)} + \sqrt{(2I_{Bn}/\beta_9)} = \sqrt{(2I_{B3}/\beta_6)} + \sqrt{(2I_{B2}/\beta_8)}$$

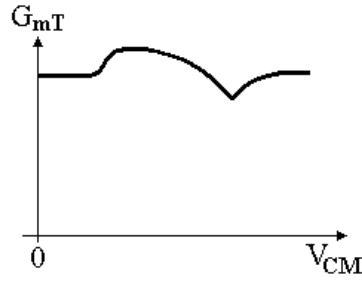
is obtained. By choosing  $\beta_5 = \beta_n$ ,  $\beta_9 = \beta_p$  and by multiplying both sides by  $\beta_n \beta_p / \sqrt{2}$ , we reach the desired result:

$$\sqrt{(\beta_n I_{Bn})} + \sqrt{(\beta_p I_{Bp})} = \beta_n \beta_p [\sqrt{(I_{B3}/\beta_6)} + \sqrt{(I_{B2}/\beta_8)}] = \text{constant}$$

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A typical small-signal  $G_{mT}$  curve along the *rail-to-rail* CM input voltage range is given on the right. Typical max. relative  $G_{mT}$  deviation is **15-20%** (*peak to peak*).

The deviations are mainly due to some imperfections (*deviations from square law,  $\beta$  differences due to body effect on nMOS input transistors, etc.*)



**Increase one  $I_B$  to  $4I_B$  when the other is OFF ( $\beta_n=\beta_p$  required) :**

By utilizing current switching, one differential pair can be forced to overtake the role of the other (when the other dif. pair is OFF). Thus the overall  $G_{mT}$  can be kept constant (*still  $\beta_n=\beta_p$  required* ⊗ ).

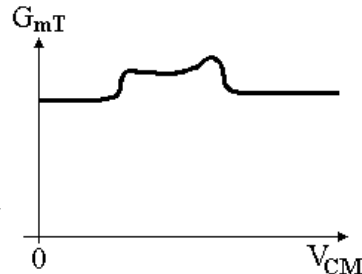
It can be estimated beforehand that, within the proximity of the current switching instants, there will be some “sudden” changes in  $G_{mT}$

Two structures will be supplied for this approach; one is below.

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$$G_{mT} = g_{mn} + g_{mp} = \sqrt{(\beta_n I_{Bn})} + \sqrt{(\beta_p I_{Bp})} = \begin{cases} \sqrt{(4\beta_n I_B)} = 2\sqrt{(\beta I_B)}, & n \text{ ON} / p \text{ OFF} \\ \sqrt{(\beta_n I_B)} + \sqrt{(\beta_p I_B)} = 2\sqrt{(\beta I_B)}, & n+p \text{ ON} \\ \sqrt{(4\beta_p I_B)} = 2\sqrt{(\beta I_B)}, & p \text{ ON} / n \text{ OFF} \end{cases}$$

As a result, if  $\beta_n=\beta_p$  equality can be achieved, an almost constant equivalent transconductance can be obtained for all regions, as shown on the right. This is a typical  $G_{mT}$  curve. The sharp transitions are due to current switching. It is obvious that, it is not easy to obtain a **fully flat** curve. **15%** max. relative error is typical.



In an alternative structure (see the figure next page), the current switching is made gradual, such that, the transitions of input pairs from ON to OFF (*and OFF to ON*) regimes are much smoother. Thus, the sharp transitions (*thus, inevitably larger relative errors*) in the  $G_{mT}$  curve are aimed to be eliminated.

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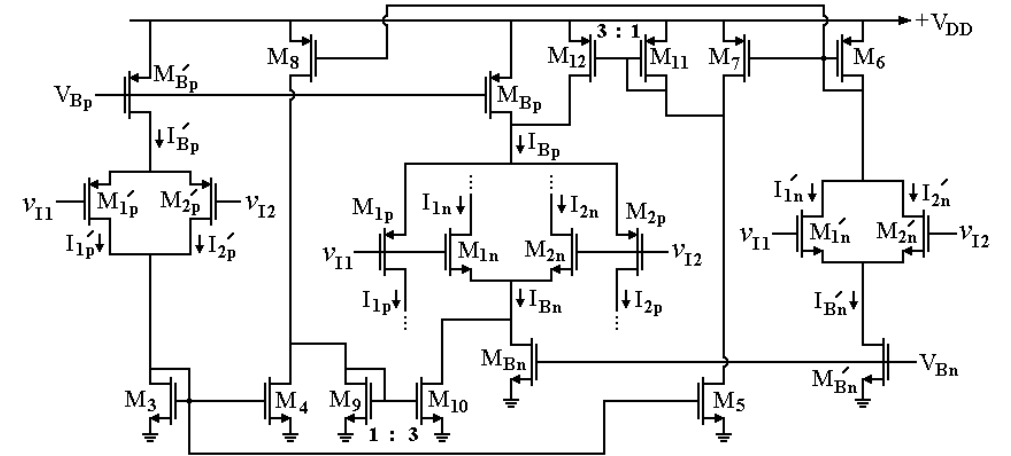
$M_7$  and  $M_8$  act as switches, biased (not controlled - *at least directly*) by  $V_{B7}$  and  $V_{B8}$ , respectively. The *direct* control of these switches are actually via the potential variations at nodes  $S_p$  and  $S_n$ .

$V_{B7}$  and  $V_{B8}$  chosen such that

- $M_7$  is ON when  $M_{1p}$ - $M_{2p}$  pair is OFF (i.e.  $V_{Sn}$  tends to GND)
  - $M_8$  is ON when  $M_{1p}$ - $M_{2p}$  pair is OFF (i.e.  $V_{Sp}$  tends to  $V_{DD}$ )
- ☞  $M_{Bn}$  and  $M_{Bp}$  are both supplying  $I_B$ .

- When both pairs are ON:  $M_7$  and  $M_8$  are OFF  $\rightarrow I_{D3}, I_{D4}, I_{D5}, I_{D6} = 0A$ . Thus, the circuit behaves like a basic *rail-to-rail* input stage.
- nMOS pair ON, pMOS pair OFF:  $M_7$  is OFF  $\rightarrow I_{D5}, I_{D6} = 0A$ . On the other hand,  $M_8$  is ON  $\rightarrow I_{D3}=I_B$  (because,  $I_{Bp}=0$ )  $\rightarrow I_{D4}=3I_{D3}=3I_B \rightarrow I_{Bn}=4I_B$
- pMOS pair ON, nMOS pair OFF:  $M_8$  is OFF  $\rightarrow I_{D3}, I_{D4} = 0A$ . On the other hand,  $M_7$  is ON  $\rightarrow |I_{D5}|=I_B$  (because,  $I_{Bn}=0$ )  $\rightarrow |I_{D6}|=3|I_{D5}|=3I_B \rightarrow I_{Bp}=4I_B$

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The auxiliary pairs  $M_{1n}'$ - $M_{2n}'$  and  $M_{1p}'$ - $M_{2p}'$  helps obtaining precise replicas of drain currents of  $M_{Bn}$  and  $M_{Bp}$ . These copies are compared and depending on which one is larger,  $I_{Bn}$  and  $I_{Bp}$  are assigned appropriate values.

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- When  $I_{Bn} > I_{Bp}$ ,  $M_9$  will receive the current difference ( $I_{Bn} - I_{Bp}$ ), thus  $I_{Bn} = I_{Bn} + 3(I_{Bn} - I_{Bp})$ ; however,  $M_{11}$  will be **OFF** (it cannot handle a current inwards, so  $M_7$  will be driven into triode region to “worship”  $M_9$ ), thus  $M_{12}$  will be **OFF**, yielding  $I_{Bp} = I_{Bp}$ .
- When  $I_{Bn} < I_{Bp}$ ,  $M_{11}$  will receive the current difference ( $I_{Bp} - I_{Bn}$ ), thus  $I_{Bp} = I_{Bp} + 3(I_{Bp} - I_{Bn})$ ; however,  $M_9$  will be **OFF** (it cannot handle a current outwards, so  $M_4$  will be driven into triode region to “worship”  $M_9$ ), thus  $M_{10}$  will be **OFF**, yielding  $I_{Bn} = I_{Bn}$ .

If nominal values (i.e. when  $M_{Bn}/M_{Bn}$  and  $M_{Bp}/M_{Bp}$  are in saturation) of  $I_{Bp}$  and  $I_{Bn}$  are set equal (equal to  $I_B$ ), then,

- When both pairs are ON and saturated  $\rightarrow I_{Bn} = I_{Bp} = I_B$ .
- When only the **n** pair is ON  $\rightarrow I_{Bn} = 4I_B$ .
- When only the **p** pair is ON  $\rightarrow I_{Bp} = 4I_B$ .

... **BUT**, in between these 3 regions, the “travel” of each tail current value from  $I_B$  to  $4I_B$  is made *gradual* for this structure.

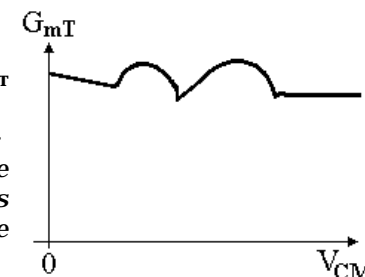
Setting  $\beta_n = \beta_p$  supplies a nominal transconductance of  $G_{mT} = 2\sqrt{(\beta I_B)}$

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On the right is a typical  $G_{mT}$  curve.

Typical value for the max. relative  $G_{mT}$  error is **10%**, which is quite sufficient.

**Note:** It may seem as if in some  $G_{mT}$  curves, the relative error is much larger. Usually the curves are “exaggerated” to supply an idea about the typical nature of the  $G_{mT}$ - $V_{CM}$  curve.



**Use a Zener diode (or equivalent) to keep  $V_{GSn} + V_{GSp}$  constant :**

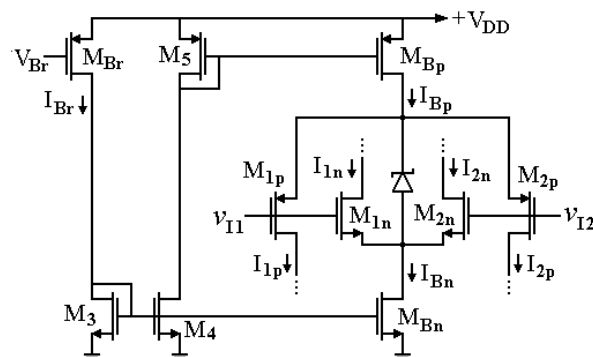
Let's recall the equivalent transconductance equation:

$$G_{mT} = g_{mn} + g_{mp} = \beta_n(V_{GSn} - V_{THn}) + \beta_p(V_{GSp} - V_{THp})$$

This equation says, “ If  $\beta_n = \beta_p$  and  $V_{THn} = V_{THp}$  can be assumed, then, keeping  $G_{mT}$  constant is reduced to keeping  $V_{GSn} + V_{GSp}$  constant”

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Keeping a voltage constant can be regarded as a “DC regulation” issue. Therefore, Zener diodes are good choices; ☹ however they are not found in every process. Nevertheless, let's use the symbol for conceptual explanation purposes.



Compared to the current-based solutions, the most important advantage of this technique is the use of less number of extra current mirrors/sources (lower power consumption).

$I_{Bp}$  and  $I_{Bn}$  must supply enough amount of current to help the Zener diode operate properly, as well the input pairs.

When  $V_{CM}$  is close to **GND**, the **n** pair is **OFF** and also Zener is **OFF** (since  $V_{Sp}$  is at a low value). Then the **p** pair will receive a tail current of  $I_{Br}$ . When  $V_{CM}$  is close to  $V_{DD}$ , the **p** pair is **OFF** and also Zener is **OFF** (since  $V_{Sn}$  is at a high value). Then the **n** pair will receive a tail current of  $I_{Br}$ .

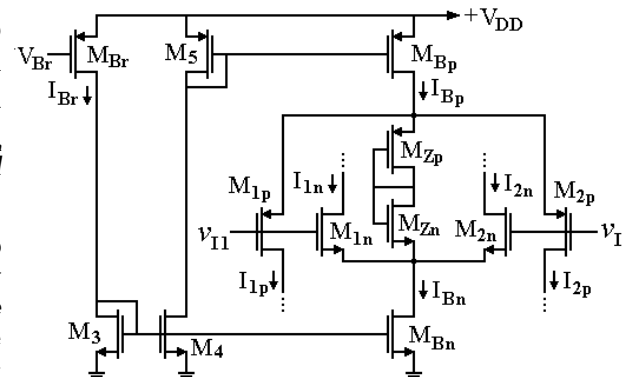
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In between, both pairs will be **ON**, each drawing **equal** tail currents (since  $\beta_n = \beta_p$  and  $V_{THn} = V_{THp}$  can be assumed) determined by the Zener voltage. Making this tail current equal to  $\frac{1}{4}I_{Br}$  is vital to obtain a constant  $G_{mT}$  (then, the Zener receives  $\frac{3}{4}I_{Br}$ ).

In the circuit below, a CMOS structure is used in place of the Zener diode, such that, when both pairs are ON, it receives  $\frac{3}{4}$  of  $I_{Br}$ .

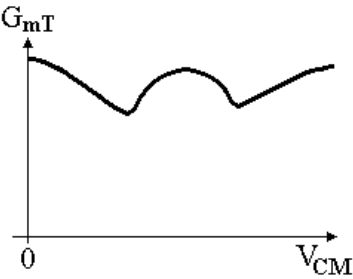
It shouldn't be hard to guess that the design must satisfy  $\beta_{zp} = 6\beta_p$  and  $\beta_{zn} = 6\beta_n$  (in fact,  $\beta_{zp} = \beta_{zn}$  should also be satisfied since  $\beta_p = \beta_n$  is aimed).

The pseudo-Zener can go OFF not sharply but only gradually (together with one of the input pairs). Therefore the  $G_{mT}$  cannot be kept satisfactorily constant.

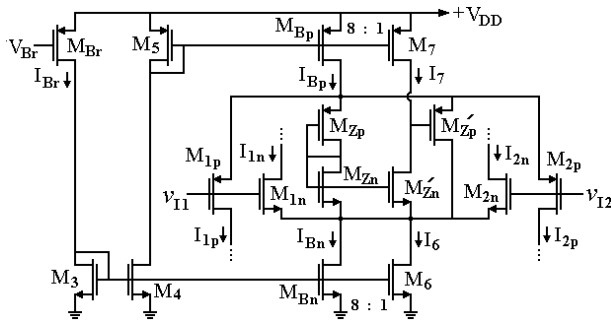


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Typical value of maximum relative  $\mathbf{G}_{\text{mT}}$  error is **20%**. Sharpening the ON-OFF transition is a must.

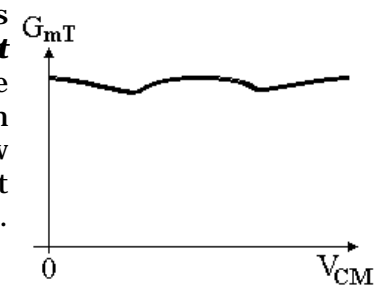


A maximum  $\mathbf{G}_{\text{mT}}$  error less than **10%** is easily achievable.



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**Insert voltage level shift between inputs of  $p$  and  $n$  pairs :**



...

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